LAYERED-FILAMENT LATTICE FOR CHEMICAL MECHANICAL POLISHING

Abstract

The polishing pad (104) is useful for polishing at least one of a magnetic, optical and semiconductor substrate (112) in the presence of a polishing medium (120). The polishing pad 104 includes multiple layers of polishing filaments (200, 300, 400, 500) stacked on a base layer (204, 404, 504) of polishing filaments, the multiple layers of polishing filaments (200, 300, 400, 500) having a sequential stacked formation with each layer of the polishing filaments being above and attached to a lower polishing filament, the multiple layers of polishing filaments (200, 300, 400, 500) being parallel to a polishing surface of the polishing pad (104) and wherein individual polishing filaments (202, 302, 402) of the multiple layers of polishing filaments (200, 300, 400, 500) are above an average of at least three polishing filaments (202, 302, 402), to form the polishing pad having an open lattice structure of interconnected polishing filaments (210, 310, 410, 510, 610).